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A combined method of DRIE and wet etching for releasing TES islands

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Releasing TES islands from a silicon substrate is the most challenging step of TES fabrication process and it limits the yield of wafers. The etching rate and surface shape of wet etching method is difficult to control, and the stop layer of silicon dioxide for deep reactive-ion etching (DRIE) is difficult to clear after releasing process. We present a combined method of DRIE and wet etching to overcome these shortages and enhance yield.

Less than 5 years of experience since completion of Ph.D

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Student (Ph.D., M.Sc. or B.Sc.)

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Primary authors: Mr GAO, Guanhua (Institute of High Energy Physics, Chinese Academy of Sciences); Mr GAO, He (Institute of High Energy Physics, Chinese Academy of Sciences(IHEP,CAS))

Presenter: Mr GAO, Guanhua (Institute of High Energy Physics, Chinese Academy of Sciences)

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